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Kind regards,

Team Nexperia

# XC7SHU04

## Inverter

Rev. 01 — 7 September 2009

Product data sheet

## 1. General description

The XC7SHU04 is a high-speed Si-gate CMOS device. It provides an inverting single stage function.

## 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - ◆ HBM JESD22-A114E: exceeds 2000 V
  - ◆ MM JESD22-A115-A: exceeds 200 V
  - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
XC7SHU04GW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
XC7SHU04GV	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SC-74A	plastic surface-mounted package; 5 leads	SOT753

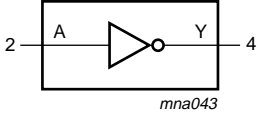
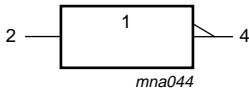
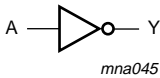
## 4. Marking

**Table 2. Marking codes**

Type number	Marking <sup>[1]</sup>
XC7SHU04GW	fD
XC7SHU04GV	fU4

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

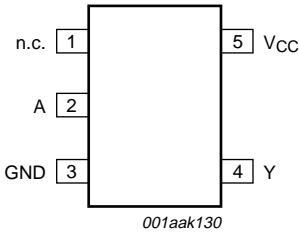
## 5. Functional diagram

		
<b>Fig 1. Logic symbol</b>	<b>Fig 2. IEC logic symbol</b>	<b>Fig 3. Logic diagram</b>

## 6. Pinning information

### 6.1 Pinning

**XC7SHU04**



**Fig 4. Pin configuration SOT353-1 and SOT753**

### 6.2 Pin description

**Table 3. Pin description**

Symbol	Pin	Description
n.c.	1	not connected
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V <sub>CC</sub>	5	supply voltage

## 7. Functional description

**Table 4. Function table**

*H = HIGH voltage level; L = LOW voltage level*

Input	Output
A	Y
L	H
H	L

## 8. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_I < -0.5$ V	-20	-	mA
$V_I$	input voltage		[1] -0.5	+7.0	V
$I_{OK}$	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	-	$\pm 20$	mA
$I_O$	output current	$-0.5$ V < $V_O$ < $V_{CC} + 0.5$ V	-	$\pm 25$	mA
$I_{CC}$	supply current		-	75	mA
$I_{GND}$	ground current		-75	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For both TSSOP5 and SC-74A packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

*Voltages are referenced to GND (ground = 0 V).*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC}$	supply voltage		2.0	5.0	5.5	V
$V_I$	input voltage		0	-	5.5	V
$V_O$	output voltage		0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.3$ V $\pm$ 0.3 V	-	-	100	ns/V
		$V_{CC} = 5.0$ V $\pm$ 0.5 V	-	-	20	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.7	-	-	1.7	-	1.7	-	V
		V <sub>CC</sub> = 3.0 V	2.4	-	-	2.4	-	2.4	-	V
		V <sub>CC</sub> = 5.5 V	4.4	-	-	4.4	-	4.4	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	-	0.3	-	0.3	-	0.3	V
		V <sub>CC</sub> = 3.0 V	-	-	0.6	-	0.6	-	0.6	V
		V <sub>CC</sub> = 5.5 V	-	-	1.1	-	1.1	-	1.1	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I <sub>O</sub> = -8.0 mA; V <sub>CC</sub> = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I <sub>O</sub> = 8.0 mA; V <sub>CC</sub> = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	1.0	-	10	-	40	μA
C <sub>I</sub>	input capacitance		-	1.5	10	-	10	-	10	pF

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**  
*GND = 0 V. For test circuit see Figure 6.*

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	propagation delay	A to Y; see Figure 5 <a href="#">[1]</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V <a href="#">[2]</a>								
		C <sub>L</sub> = 15 pF	-	3.4	7.1	1.0	8.5	1.0	10.0	ns
		C <sub>L</sub> = 50 pF	-	4.9	10.6	1.0	12.0	1.0	13.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V <a href="#">[3]</a>								
		C <sub>L</sub> = 15 pF	-	2.6	5.5	1.0	6.0	1.0	7.0	ns
		C <sub>L</sub> = 50 pF	-	3.6	7.0	1.0	8.0	1.0	9.0	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; V <sub>I</sub> = GND to V <sub>CC</sub>	<a href="#">[4]</a>	-	14	-	-	-	-	pF

[1] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.

[2] Typical values are measured at V<sub>CC</sub> = 3.3 V.

[3] Typical values are measured at V<sub>CC</sub> = 5.0 V.

[4] C<sub>PD</sub> is used to determine the dynamic power dissipation P<sub>D</sub> (μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

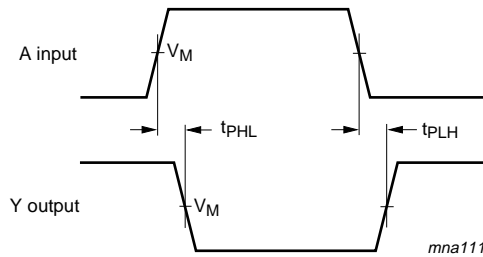
f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in Volts.

**12. Waveforms**

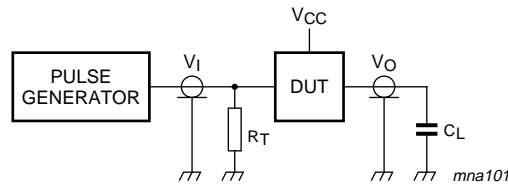


Measurement points are given in [Table 9](#).

**Fig 5. Input (A) to output (Y) propagation delays**

**Table 9. Measurement point**

Type	Input	Input	Output
	$V_I$	$V_M$	$V_M$
XC7SHU04	GND to $V_{CC}$	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in [Table 10](#). Definitions for test circuit:

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

**Fig 6. Load circuitry for switching times**

**Table 10. Test data**

Type	Input		Load	Test
	$V_I$	$t_r, t_f$	$C_L$	
XC7SHU04	$V_{CC}$	$\leq 3.0$ ns	15 pF, 50 pF	$t_{PLH}, t_{PHL}$

### 13. Typical transfer characteristics

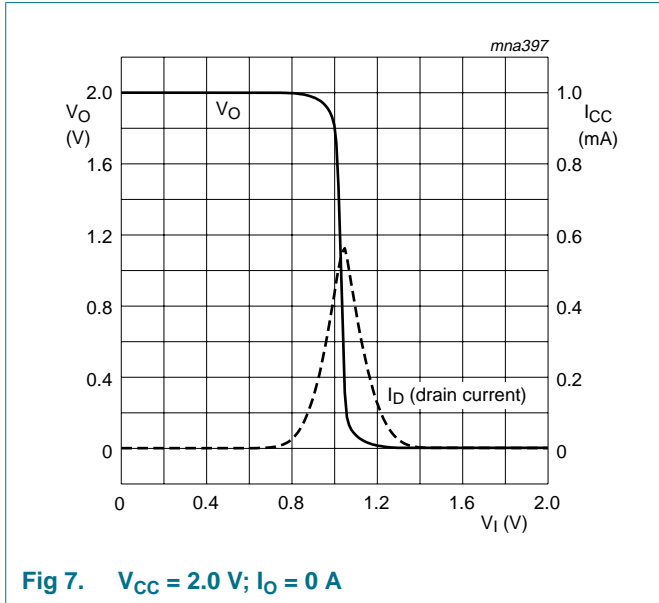


Fig 7.  $V_{CC} = 2.0 \text{ V}; I_O = 0 \text{ A}$

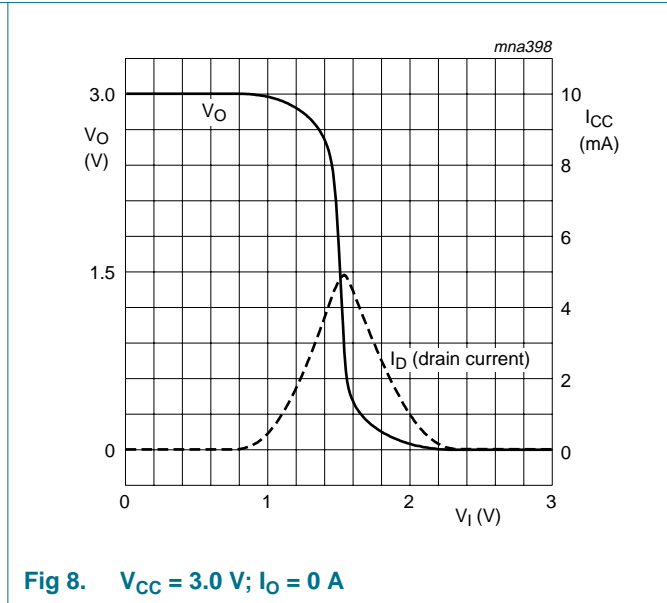


Fig 8.  $V_{CC} = 3.0 \text{ V}; I_O = 0 \text{ A}$

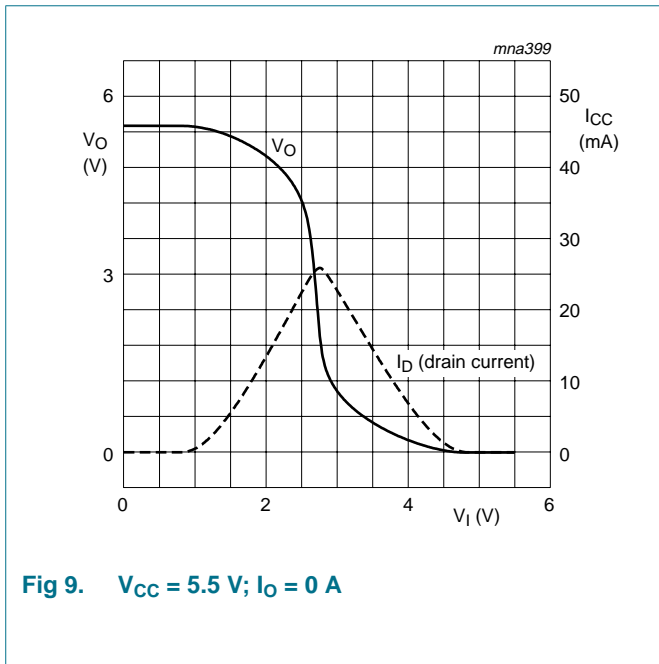


Fig 9.  $V_{CC} = 5.5 \text{ V}; I_O = 0 \text{ A}$

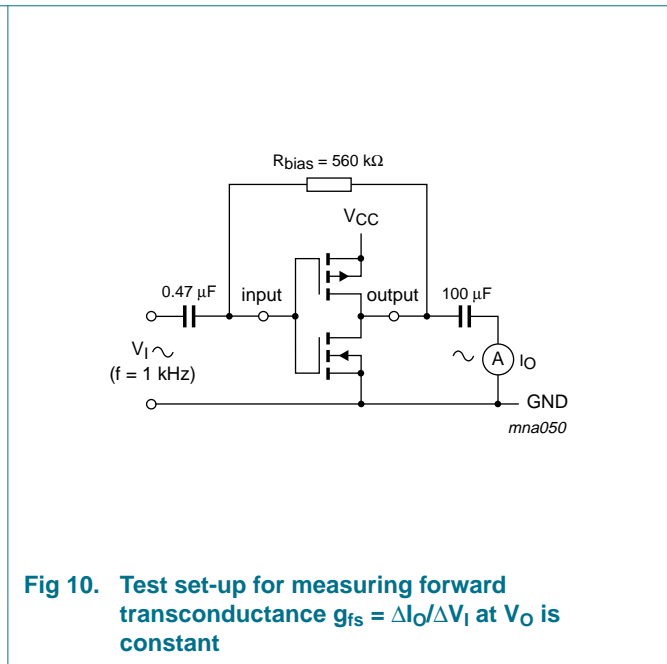


Fig 10. Test set-up for measuring forward transconductance  $g_{fs} = \Delta I_O / \Delta V_I$  at  $V_O$  is constant



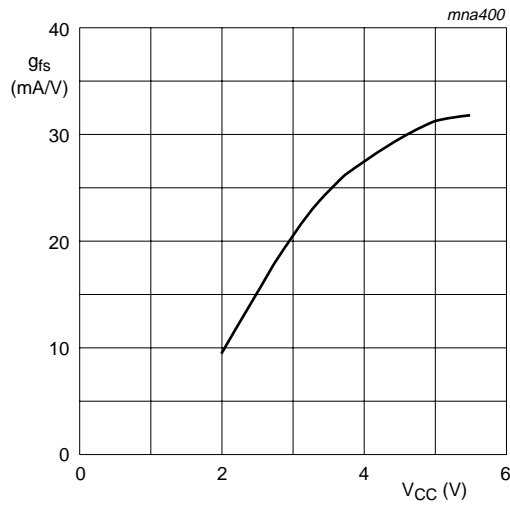


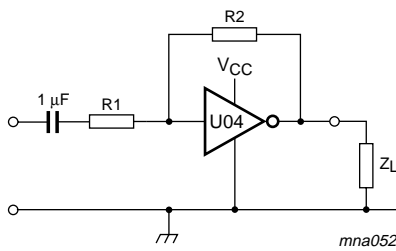
Fig 11. Typical forward transconductance  $g_{fs}$  as a function of the supply voltage at  $T_{amb} = 25\text{ }^\circ\text{C}$

### 14. Application information

Some applications are:

- Linear amplifier (see [Figure 12](#))
- In crystal oscillator design (see [Figure 13](#))

**Remark:** All values given are typical unless otherwise specified.



Maximum  $V_{o(p-p)} = V_{CC} - 1.5\text{ V}$  centered at  $0.5 \times V_{CC}$ .

$$G_v = -\frac{G_{ol}}{1 + \frac{R1}{R2}(1 + G_{ol})}$$

$G_{ol}$  = open loop gain

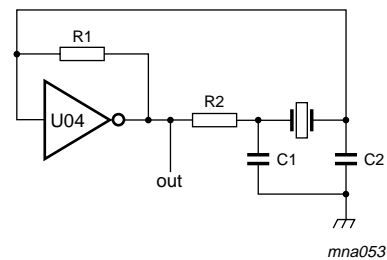
$G_v$  = voltage gain

$R1 \geq 3\text{ k}\Omega$ ,  $R2 \leq 1\text{ M}\Omega$

$Z_L > 10\text{ k}\Omega$ ;  $G_{ol} = 20$  (typ.)

Typical unity gain bandwidth product is 5 MHz.

Fig 12. Used as a linear amplifier



$C1 = 47\text{ pF}$  (typ.)

$C2 = 22\text{ pF}$  (typ.)

$R1 = 1\text{ M}\Omega$  to  $10\text{ M}\Omega$  (typ.)

$R2$  optimum value depends on the frequency and required stability against changes in  $V_{CC}$  or average minimum  $I_{CC}$  ( $I_{CC}$  is typically 2 mA at  $V_{CC} = 3\text{ V}$  and  $f = 1\text{ MHz}$ ).

Fig 13. Crystal oscillator configuration

**Table 11. External components for resonator (f < 1 MHz)***All values given are typical and must be used as an initial set-up.*

Frequency	R1	R2	C1	C2
10 kHz to 15.9 kHz	22 M $\Omega$	220 k $\Omega$	56 pF	20 pF
16 kHz to 24.9 kHz	22 M $\Omega$	220 k $\Omega$	56 pF	10 pF
25 kHz to 54.9 kHz	22 M $\Omega$	100 k $\Omega$	56 pF	10 pF
55 kHz to 129.9 kHz	22 M $\Omega$	100 k $\Omega$	47 pF	5 pF
130 kHz to 199.9 kHz	22 M $\Omega$	47 k $\Omega$	47 pF	5 pF
200 kHz to 349.9 kHz	22 M $\Omega$	47 k $\Omega$	47 pF	5 pF
350 kHz to 600 kHz	22 M $\Omega$	47 k $\Omega$	47 pF	5 pF

**Table 12. Optimum value for R2**

Frequency	R2	Optimum for
3 kHz	2.0 k $\Omega$	minimum required I <sub>CC</sub>
	8.0 k $\Omega$	minimum influence due to change in V <sub>CC</sub>
6 kHz	1.0 k $\Omega$	minimum required I <sub>CC</sub>
	4.7 k $\Omega$	minimum influence by V <sub>CC</sub>
10 kHz	0.5 k $\Omega$	minimum required I <sub>CC</sub>
	2.0 k $\Omega$	minimum influence by V <sub>CC</sub>
14 kHz	0.5 k $\Omega$	minimum required I <sub>CC</sub>
	1.0 k $\Omega$	minimum influence by V <sub>CC</sub>
> 14 kHz	-	replace R2 by C3 with a typical value of 35 pF

15. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

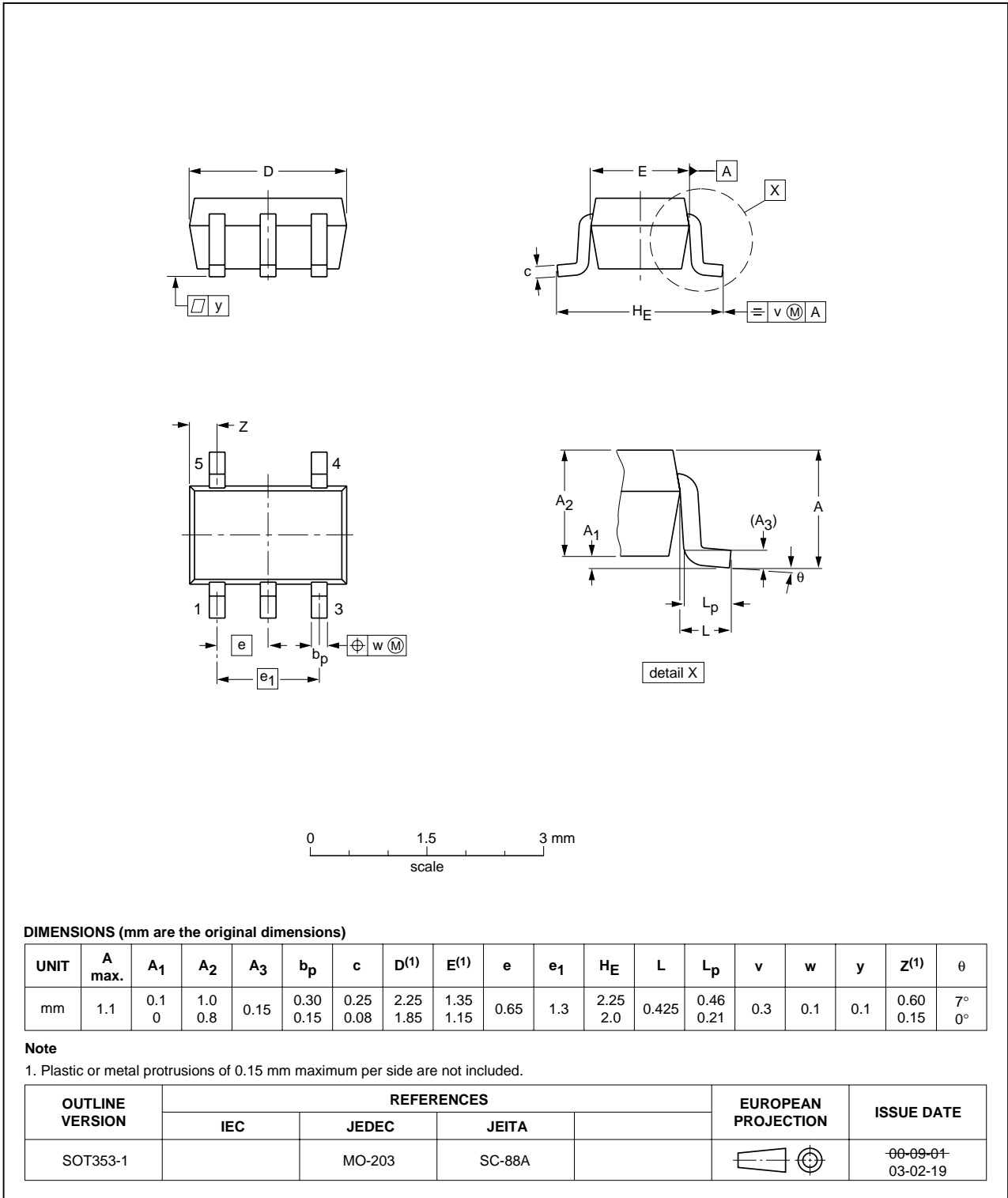


Fig 14. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

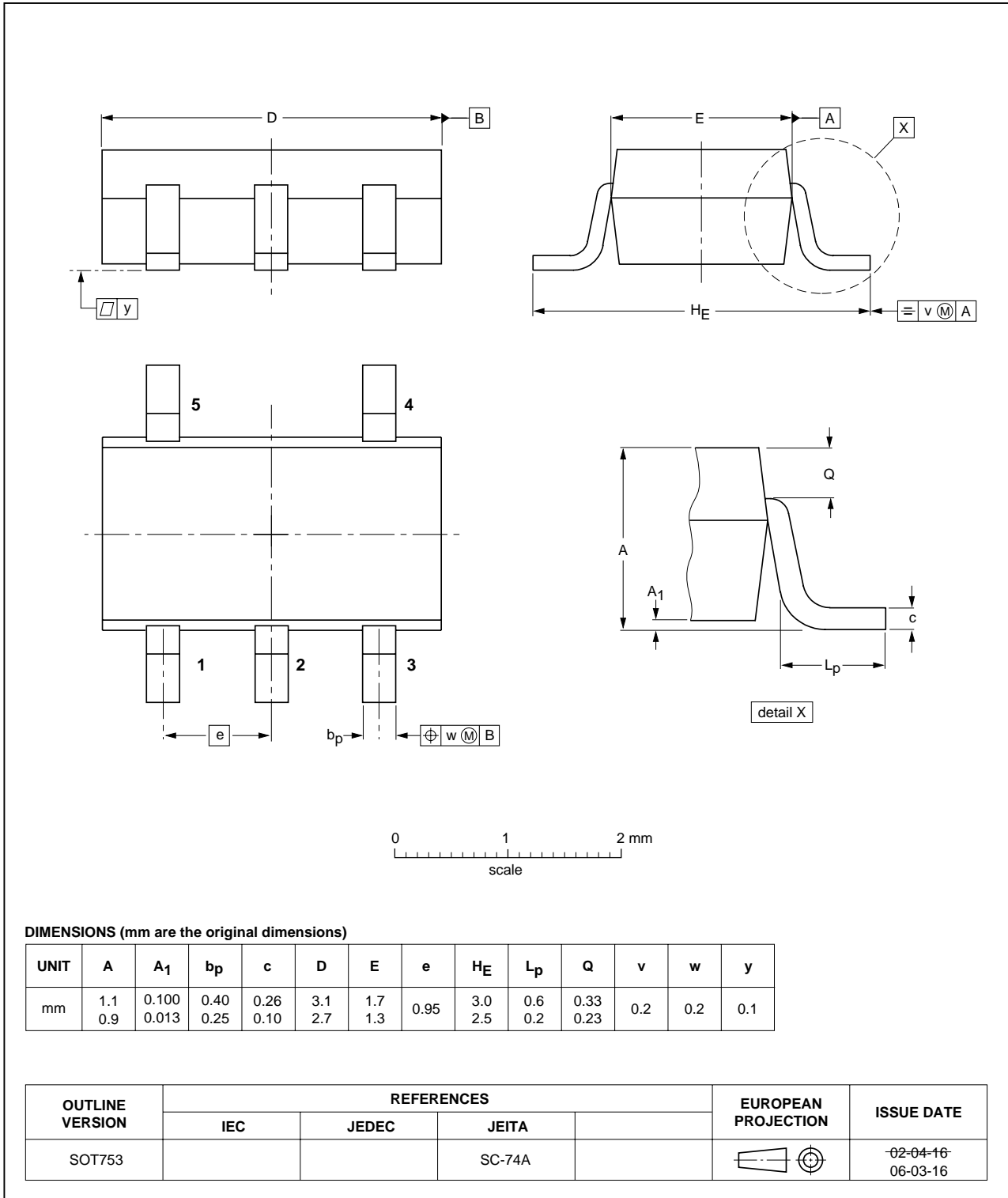


Fig 15. Package outline SOT753 (SC-74A)

## 16. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

## 17. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
XC7SHU04_1	20090907	Product data sheet	-	-

## 18. Legal information

### 18.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**20. Contents**

1 **General description** . . . . . 1

2 **Features** . . . . . 1

3 **Ordering information** . . . . . 1

4 **Marking** . . . . . 2

5 **Functional diagram** . . . . . 2

6 **Pinning information** . . . . . 2

6.1 Pinning . . . . . 2

6.2 Pin description . . . . . 2

7 **Functional description** . . . . . 3

8 **Limiting values** . . . . . 3

9 **Recommended operating conditions** . . . . . 3

10 **Static characteristics** . . . . . 4

11 **Dynamic characteristics** . . . . . 5

12 **Waveforms** . . . . . 6

13 **Typical transfer characteristics** . . . . . 7

14 **Application information** . . . . . 8

15 **Package outline** . . . . . 10

16 **Abbreviations** . . . . . 12

17 **Revision history** . . . . . 12

18 **Legal information** . . . . . 13

18.1 Data sheet status . . . . . 13

18.2 Definitions . . . . . 13

18.3 Disclaimers . . . . . 13

18.4 Trademarks . . . . . 13

19 **Contact information** . . . . . 13

20 **Contents** . . . . . 14

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